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Contents

EUV SCANNER AND IMAGING I

- 11854 05 Simulation of polychromatic effects in high NA EUV lithography (Invited Paper) [11854-20]
- 11854 06 Impact of mask corner rounding on pitch 40 nm contact hole variability [11854-48]

EUV PROCESS AND MATERIALS I

- 11854 09 Development of fluoro-free surfactant rinse solutions for EUV photoresists [11854-54]

EUV PATTERNING SOLUTIONS I

- 11854 0A Towards high NA patterning readiness: materials, processes and etch transfer for P24 Line Space [11854-47]
- 11854 0C 28nm-pitch Ru interconnects patterned with a 0.33NA-EUV single exposure [11854-22]
- 11854 0D Analysis of advanced technology nodes and h-NA EUV introduction: a cost perspective [11854-8]

EUV SCANNER AND IMAGING II

- 11854 0H Pupil optimization for after etch defectivity: what imaging metrics matter? (Invited Paper) [11854-33]
- 11854 0I Contribution of mask roughness in stochasticity of high-NA EUV imaging [11854-50]

EUV LIGHT SOURCE

- 11854 0K Update of >300W high power LPP-EUV source challenge IV for semiconductor HVM [11854-5]

NEW EUV MASK TECHNOLOGY I

- 11854 0S Small scale, big impact: the world's thinnest and strongest free-standing carbon nanotube membrane [11854-3]
- 11854 0T Exploration of alternative mask for 0.33NA EUV single patterning at pitch 28nm [11854-2]

EUV PATTERNING SOLUTIONS II

- 11854 0Y Deep learning-based defect detection using large FOV SEM for 28 nm pitch BEOL layer patterned with 0.33NA single exposure EUV [11854-27]
- 11854 0Z Printability and propagation of stochastic defects through a study of defects programmed on EUV mask [11854-52]
- 11854 10 High NA EUV: a challenge for metrology, an opportunity for atomic force microscopy [11854-43]
- 11854 11 Unsupervised machine learning based SEM image denoising for robust contour detection [11854-25]

NEW EUV MASK TECHNOLOGY II

- 11854 12 Optimizations aspects for EUV low-k1 logic with the low-n mask (Invited Paper) [11854-38]
- 11854 14 First results of EUV-scanner compatibility tests performed on novel 'high-NA' reticle absorber materials [11854-19]
- 11854 15 Comparison of deposition techniques for Mo/Si reflective multilayers for EUV mask blanks [11854-34]
- 11854 16 Classification of EUV masks based on the ratio of the complex refractive index $k/(1-n)$ [11854-49]

POSTER SESSION I

- 11854 18 iN5 EUV single expose patterning evaluation for via layers [11854-23]
- 11854 19 Design and realization of an in-lab EUV dual beamline for industrial and scientific applications [11854-21]
- 11854 1B New metrology technique for measuring wafer geometry on a full 300mm silicon wafer [11854-57]